

REMARKS

Claims 3-6 are pending. Claims 5 and 6 have been amended to overcome the 35 USC 112, first paragraph, rejection. No new matter is presented.

Claims 3-6 are rejected under 35 USC 112, first paragraph, as containing subject matter which was not described in the specification in such a way as to enable one skilled in the art to make and/or use the invention. This rejection is respectfully traversed in part and overcome in part by amendment.

As previously asserted, claims 3 and 4 *do not* recite "an absolute value the select voltage is not larger than an absolute value of the negative voltage applied to the substrate or well of the nonvolatile semiconductor storage device." Furthermore, these claims do not depend from any claims which recite this feature. Thus, the rejection of claims 3 and 4 under 35 USC 112, first paragraph, is completely improper and should be withdrawn. The Examiner has previously failed to respond to this assertion and his attention to this matter is requested at this time.

Claims 5 and 6 have been amended to recite that an absolute value the select voltage is equal to an absolute value of the negative voltage applied to the substrate or well of the nonvolatile semiconductor storage device. As admitted by the Examiner, this feature is supported by the specification.

Accordingly, Applicant requests that this rejection be withdrawn.

Since the Examiner previously stated in the Office Action of April 23, 2002 that claims 3-6 were allowable because the prior art does not teach the claimed row decoder, all claims should be in condition for allowance.

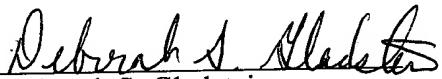
Applicant respectfully requests that the amendments to claims 5 and 6 be entered in this after-final amendment because they do not recite any additional features which would require any further search and/or consideration since the Examiner has already considered the limitation that the absolute values of the voltages are the same.

Attached hereto is a marked-up version of the changes made by this amendment, captioned "Version with markings to show changes made".

In the event that the transmittal letter is separated from this document and the Patent and Trademark Office determines that an extension and/or other relief is required, applicant petitions for any required relief including extensions of time and authorizes the Commissioner to charge the cost of such petitions and/or other fees due in connection with the filing of this document to Deposit Account No. 03-1952 referencing 204552018400.

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Respectfully submitted,

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

Amend claims 5 and 6 as follows:

5. (Amended) The row decoder according to Claim 3, wherein
in the erase mode, the select voltage is a positive voltage, while the non-select voltage is
a negative voltage; and
an absolute value the select voltage is [not larger than] equal to an absolute value of the
negative voltage applied to the substrate or well of the nonvolatile semiconductor storage device.

6. (Amended) The row decoder according to Claim 4, wherein
in the erase mode, the select voltage is a positive voltage, while the non-select voltage is
a negative voltage; and
an absolute value the select voltage is [not larger than] equal to an absolute value of the
negative voltage applied to the substrate or well of the nonvolatile semiconductor storage device.